MP2236C

18V, 6A, High-Efficiency, FCCM Synchronous Step-Down Converter

DESCRIPTION

The MP2236C is a high-frequency, synchronous, rectified, step-down, switch-mode converter. The MP2236C offers a fully integrated solution that achieves up to 6A of continuous output current (I_{OUT}), with excellent load and line regulation across a wide input supply range.

Constant-on-time (COT) control operation provides fast transient response. Full protection features include hiccup over-current protection (OCP) and thermal shutdown.

The MP2236C requires a minimal number of readily available, standard external components, and is available in a space-saving TSOT23-8 package.

FEATURES

- Forced Continuous Conduction Mode (FCCM)
- Wide 3V to 18V Operating Input Voltage (V_{IN}) Range
- 6A Continuous Output Current (I_{OUT})
- 25mΩ and 12mΩ Low On Resistance ($R_{DS(ON)}$) Internal Power MOSFETs
- Default 600mV Reference Voltage (V_{FB})
- Adjustable Output Voltage (V_{OUT})
- 600kHz Switching Frequency (f_{SW})
- On time (t_{ON}) Extension
- Hiccup Over-Current Protection (OCP)
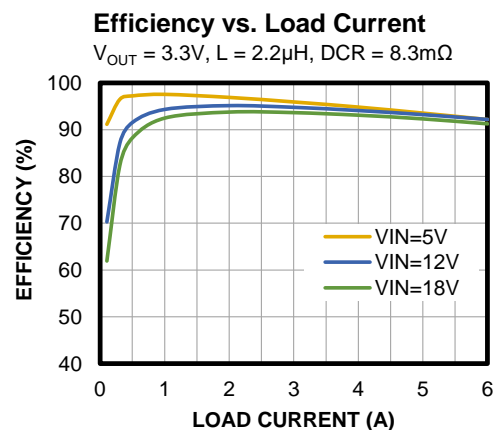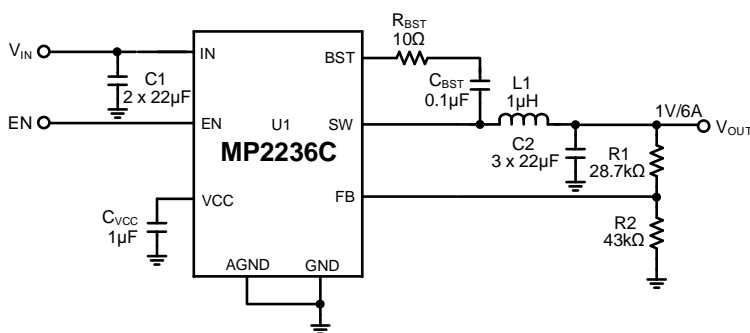- Thermal Shutdown Protection
- Available in a TSOT23-8 Package

MPL — Optimized Performance with MPS Inductor MPL-AL6050 Series

APPLICATIONS

- Flat-Panel Televisions and Monitors
- Digital TV Power Supplies
- Digital Set-Top Boxes
- Distributed Power Systems

TYPICAL APPLICATION

Efficiency vs. Load Current
V_{OUT} = 3.3V, L = 2.2µH, DCR = 8.3mΩ

ORDERING INFORMATION

Part Number*	Package	Top Marking	MSL Rating
MP2236CGJ	TSOT23-8	*See Below*	1

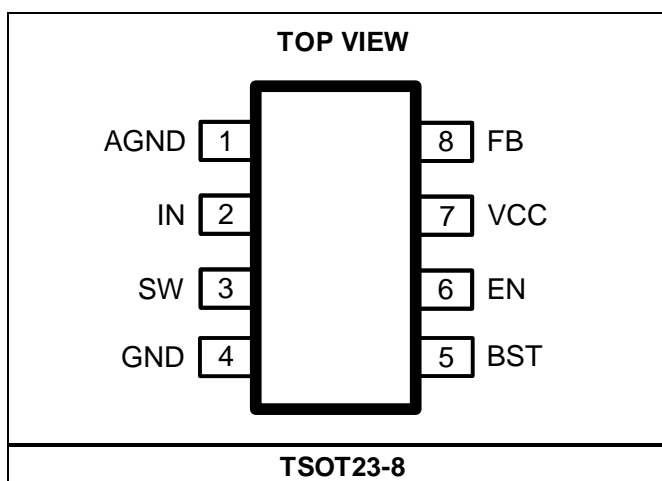For Tape & Reel, add suffix -Z (e.g. MP2236CGJ-Z).

TOP MARKING

| BRMY

BRM: Product code of MP2236CGJ
Y: Year code

PACKAGE REFERENCE

TOP VIEW

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AGND  [1]        [8]  FB
  IN  [2]        [7]  VCC
  SW  [3]        [6]  EN
 GND  [4]        [5]  BST
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TSOT23-8

PIN FUNCTIONS

Pin #	Name	Description
1	AGND	**Analog ground.** Connect AGND to GND using a short and wide PCB trace.
2	IN	**Supply voltage.** The MP2236C operates from a 3V to 18V input rail. Use a ceramic capacitor to decouple the input rail. Connect the IN pin using a wide PCB trace.
3	SW	**Switch output.** Connect the SW pin using a wide PCB trace.
4	GND	**System power ground.** The GND pin is the regulated output voltage (V_{OUT})'s reference ground, and requires special consideration in the PCB layout. Connect GND to the ground plane with copper traces and vias.
5	BST	**Bootstrap.** Connect a 0.1µF capacitor between SW and BST to form a floating supply across the high-side MOSFET (HS-FET) driver.
6	EN	**Enable.** Drive the EN pin high to enable the MP2236C. EN has a 2MΩ pull-down resistor to GND.
7	VCC	**Internal bias supply.** Decouple the VCC pin with a 1µF capacitor. The VCC capacitor should be placed close to VCC and GND.
8	FB	**Feedback.** Connect the FB pin to the external resistor divider's tap from the output to GND to set V_{OUT}.

ABSOLUTE MAXIMUM RATINGS [1]

V_{IN}.. -0.3V to +20V
V_{SW} .... -0.3V (-6.5V for <10ns)
……………………….to V_{IN} + 0.7V (25V for <25ns)
V_{BST}...V_{SW} + 4V
V_{EN}.. 20V
All other pins .... -0.3V to +4V
Continuous power dissipation (T_A = 25°C) [2] [5]
TSOT23-8 .... 1.89W
Junction temperature .... 150°C
Lead temperature..................................... 260°C
Storage temperature ....-65°C to +150°C

ESD Ratings

Human body model (HBM) ....±2000V
Charged device model (CDM) ....±750V

Recommended Operating Conditions [3]

Supply voltage (V_{IN}) .... 3V to 18V
Output voltage (V_{OUT})........................ 0.6V to 8V
……………………………………or V_{IN} x D_{MAX} [4]
Operating junction temp (T_J).....-40°C to +125°C

Thermal Resistance

	θ_{JA}	θ_{JC}	
TSOT23-8			
EVL2236C-J-00A [5]	66	23	°C/W
JESD51-7 [6]	100	55	°C/W

Notes:

1) Exceeding these ratings may damage the device.
2) The maximum allowable power dissipation is a function of the maximum junction temperature, T_J (MAX), the junction-to-ambient thermal resistance, θ_{JA}, and the ambient temperature, T_A. The maximum allowable continuous power dissipation at any ambient temperature is calculated by P_D (MAX) = (T_J (MAX) - T_A) / θ_{JA}. Exceeding the maximum allowable power dissipation can generate an excessive die temperature, which may cause the regulator to go into thermal shutdown. Internal thermal shutdown circuitry protects the device from permanent damage.
3) The device is not guaranteed to function outside of its operating conditions.
4) For more information about D_{MAX}, see the Low-Dropout (LDO) Operation section on page 12.
5) Measured on the EVL2236C-J-00A, a 4-layer PCB (63.5mmx63.5mm).
6) The value of θ_{JA} given in this table is only valid for comparison with other packages and cannot be used for design purposes. These values were calculated in accordance with JESD51-7, and simulated on a specified JEDEC board. They do not represent the performance obtained in an actual application.

ELECTRICAL CHARACTERISTICS

V_{IN} = 12V, T_J = -40°C to +125°C [7], typical value is tested at T_J = 25°C, unless otherwise noted.

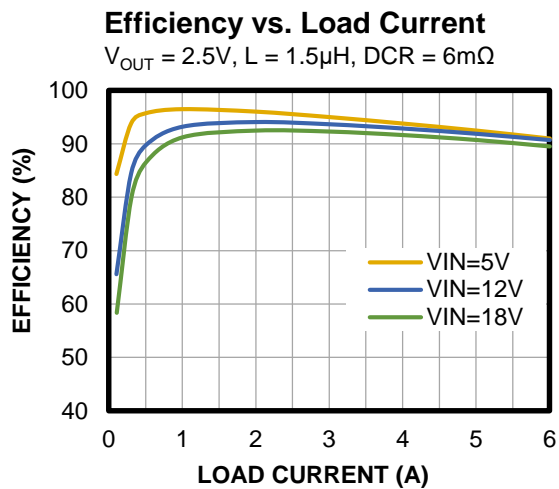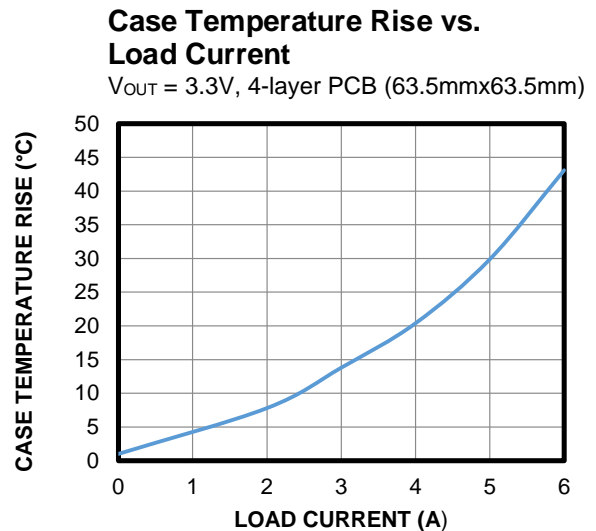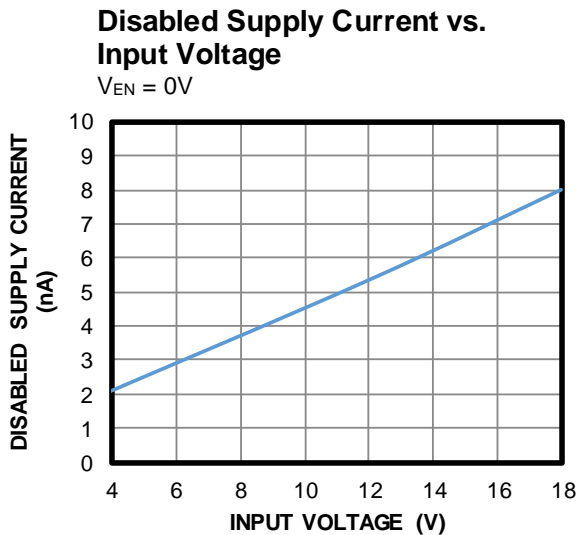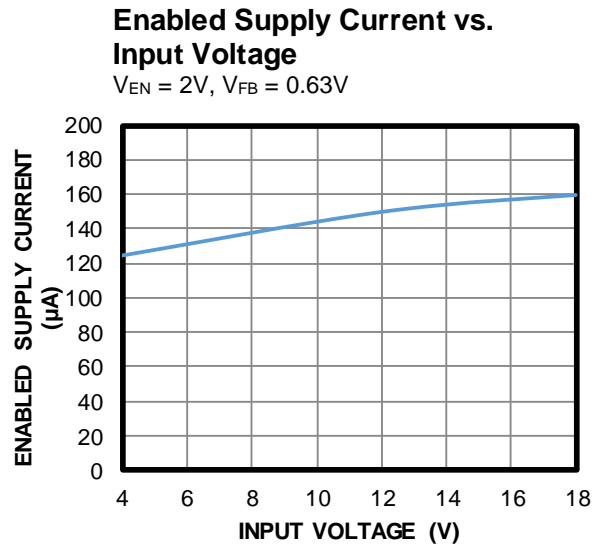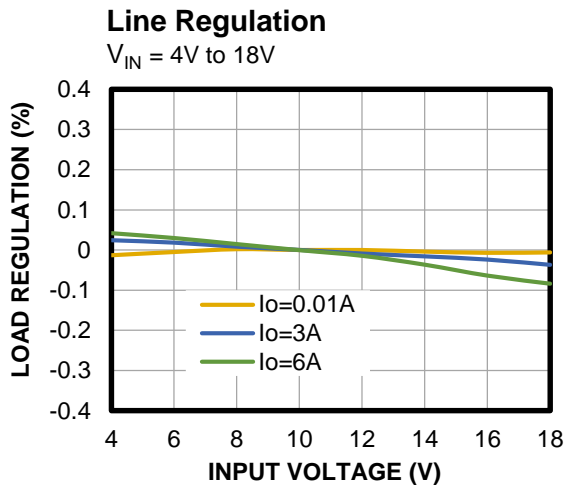| Parameter	Symbol	Condition	Min	Typ	Max	Units
Shutdown supply current	I_{IN}	V_{EN} = 0V, T_J = 25°C			1	µA
Quiescent supply current	I_Q	V_{FB} = 0.63V		550	650	µA
High-side MOSFET (HS-FET) on resistance	$R_{DS(ON)\_HS}$	V_{BST-SW} = 3.3V		25		mΩ
Low-side MOSFET (LS-FET) on resistance	$R_{DS(ON)\_LS}$			12		mΩ
Switch leakage	SW_{LKG}	V_{EN} = 0V, V_{SW} = 0V, T_J = 25°C			1	µA
Low-side (LS) valley current limit	I_{LIMIT_L}		6	7.5		A
Switching frequency	f_{SW}	V_{IN} = 12V, V_{OUT} = 3.3V	480	600	720	kHz
Minimum off time [8]	t_{OFF_MIN}			170		ns
Minimum on time [8]	t_{ON_MIN}			70		ns
Reference voltage	V_{FB}	T_J = 25°C	594	600	606	mV
		T_J = -40°C to +125°C	591	600	609	mV
Feedback (FB) current	I_{FB}	V_{FB} = 0.63V		10	50	nA
Enable (EN) rising threshold	V_{EN_RISING}		1.12	1.2	1.28	V
EN hysteresis	V_{EN_HYS}			200		mV
EN to GND pull-down resistor	R_{EN}	V_{EN} = 2V		2		MΩ
V_{IN} under-voltage lockout (UVLO) rising threshold	$V_{IN\_UVLO\_RISING}$		2.7	2.8	2.95	V
V_{IN} UVLO threshold hysteresis	$V_{IN\_UVLO\_HYS}$			300		mV
VCC regulator voltage	V_{CC}	I_{CC} = 5mA		3.5		V
Under-voltage protection (UVP) threshold 1 [8]	UVP_{TH1}	Hiccup entry		80%		V_{REF}
Soft-start time	t_{SS}	T_J = 25°C, V_{OUT} from 10% to 90%	0.5	1	1.5	ms
Thermal shutdown [8]	T_{SD}			150		°C
Thermal hysteresis [8]	T_{SD_HYS}			20		°C

Notes:

7) Not tested in production. Guaranteed by over-temperature correlation.
8) Derived by sample characterization. Not tested in production.

TYPICAL CHARACTERISTICS

V_{IN} = 12V, V_{OUT} = 1V, T_A = 25°C, unless otherwise noted.

**Efficiency vs. Load Current**
V_{OUT} = 5V, L = 3.3µH, DCR = 11.7mΩ

Efficiency vs. Load Current
V_{OUT} = 3.3V, L = 2.2µH, DCR = 8.3mΩ

Efficiency vs. Load Current
V_{OUT} = 2.5V, L = 1.5µH, DCR = 6mΩ

Efficiency vs. Load Current
V_{OUT} = 1.8V, L = 1.5µH, DCR = 6mΩ

Efficiency vs. Load Current
V_{OUT} = 1V, L = 1µH, DCR = 4.3mΩ

Load Regulation
I_{OUT} = 0.01A to 6A

TYPICAL CHARACTERISTICS *(continued)*

V_{IN} = 12V, V_{OUT} = 1V, T_A = 25°C, unless otherwise noted.

Line Regulation
V_{IN} = 4V to 18V

Enabled Supply Current vs. Input Voltage
V_{EN} = 2V, V_{FB} = 0.63V

Disabled Supply Current vs. Input Voltage
V_{EN} = 0V

Case Temperature Rise vs. Load Current
V_{OUT} = 3.3V, 4-layer PCB (63.5mmx63.5mm)

Input Voltage Threshold vs. Temperature

EN Threshold vs. Temperature

TYPICAL CHARACTERISTICS *(continued)*

V_{IN} = 12V, V_{OUT} = 1V, T_A = 25°C, unless otherwise noted.

Switching Frequency vs. Temperature
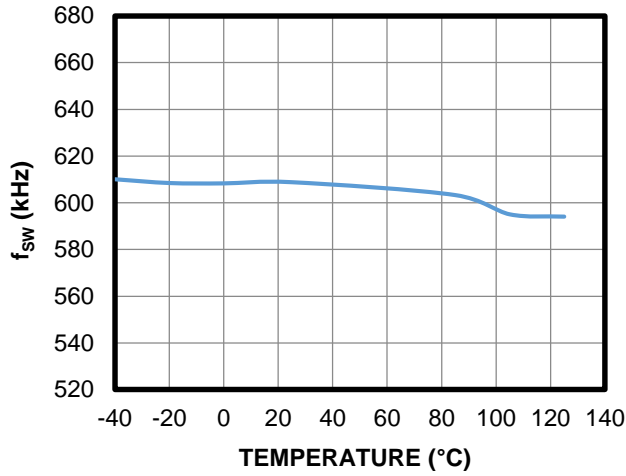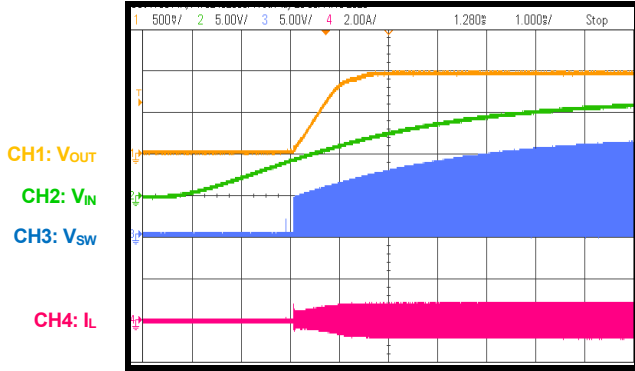
FB Voltage vs. Temperature
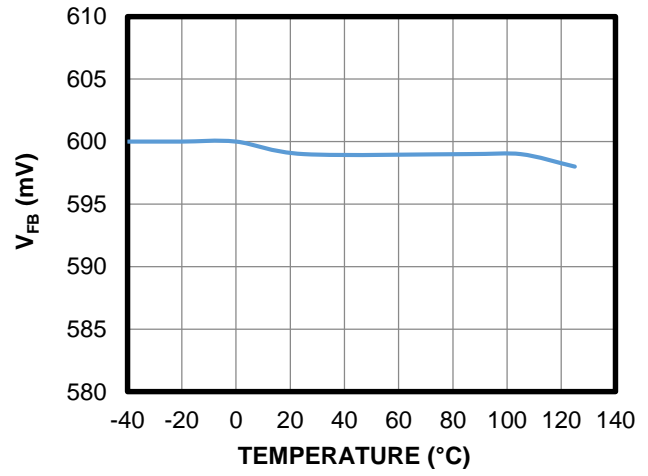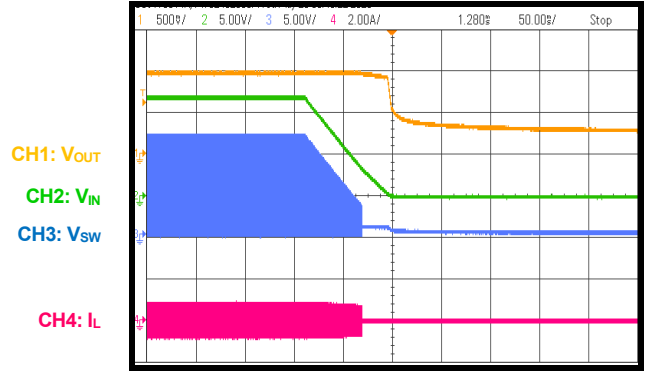
LS Valley Current Limit vs. Temperature
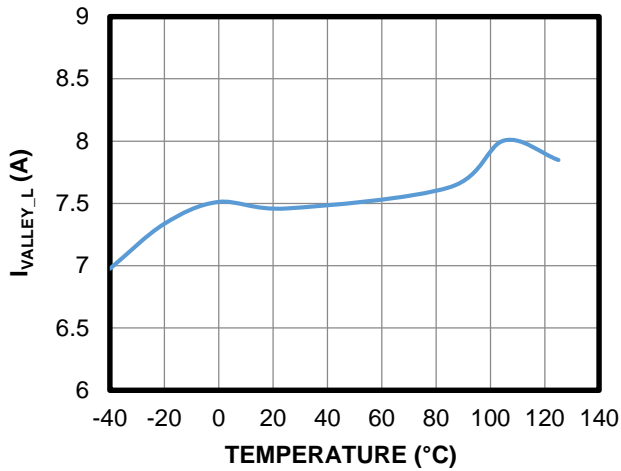
TYPICAL PERFORMANCE CHARACTERISTICS

Performance waveforms are tested on the evaluation board from the Design Example section on page 15. V_{IN} = 12V, V_{OUT} = 1V, T_A = 25°C, unless otherwise noted.
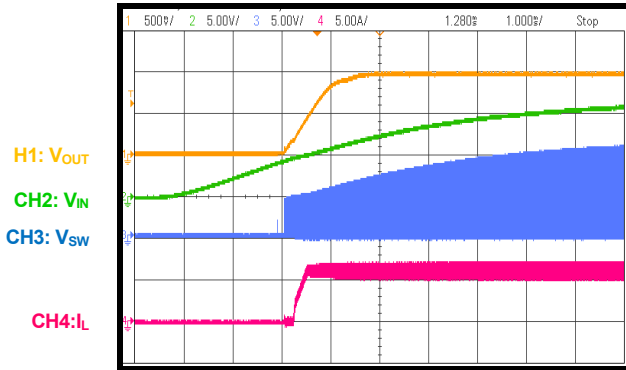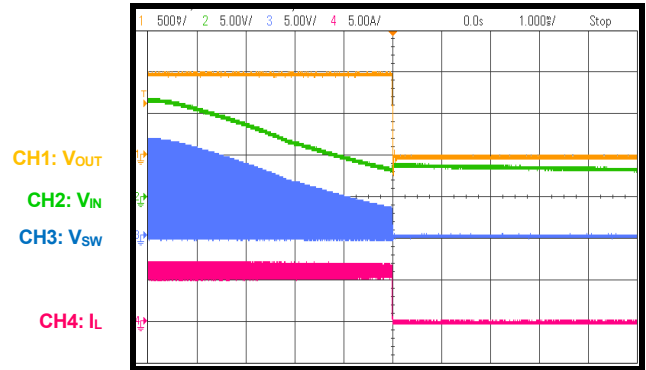
Start-Up through V_{IN}
I_{OUT} = 0A

CH1: V_{OUT}
CH2: V_{IN}
CH3: V_{SW}
CH4: I_L

Shutdown through V_{IN}
I_{OUT} = 0A

CH1: V_{OUT}
CH2: V_{IN}
CH3: V_{SW}
CH4: I_L

Start-Up through V_{IN}
I_{OUT} = 6A

H1: V_{OUT}
CH2: V_{IN}
CH3: V_{SW}
CH4: I_L

Shutdown through V_{IN}
I_{OUT} = 6A

CH1: V_{OUT}
CH2: V_{IN}
CH3: V_{SW}
CH4: I_L

Start-Up through EN
I_{OUT} = 0A

CH1: V_{OUT}
CH2: V_{EN}
CH3: V_{SW}
CH4: I_L

Shutdown through EN
I_{OUT} = 0A

CH1: V_{OUT}
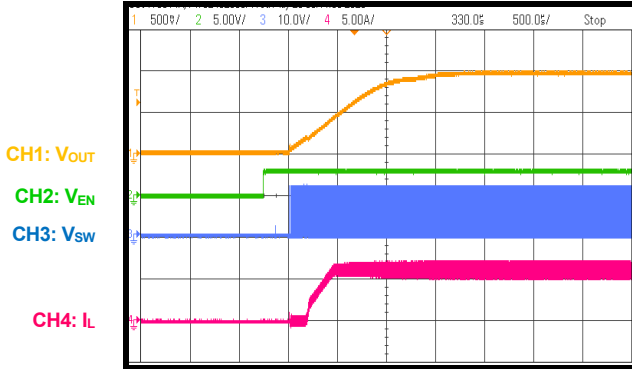CH2: V_{EN}
CH3: V_{SW}
CH4: I_L

TYPICAL PERFORMANCE CHARACTERISTICS *(continued)*

Performance waveforms are tested on the evaluation board from the Design Example section on page 15. V_{IN} = 12V, V_{OUT} = 1V, T_A = 25°C, unless otherwise noted.
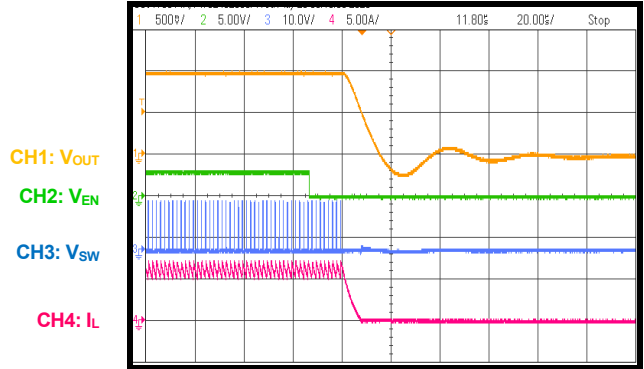
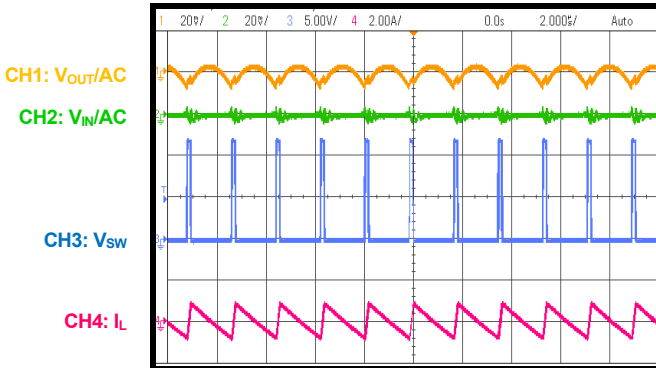### Start-Up through EN
I_{OUT} = 6A
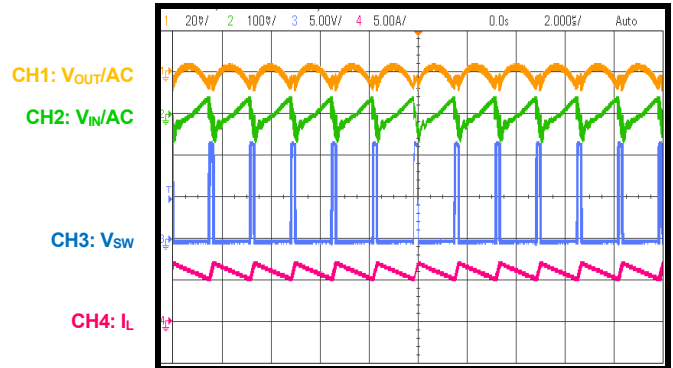
Shutdown through EN
I_{OUT} = 6A

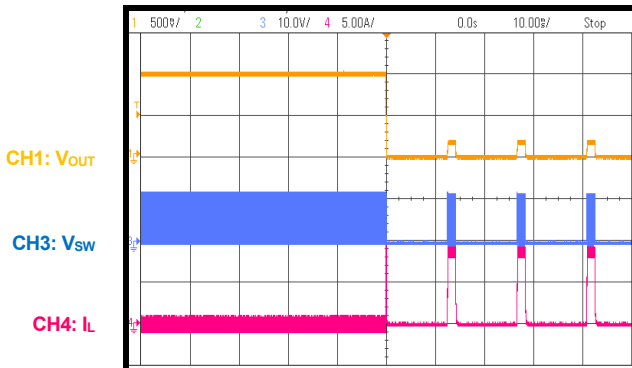### Input and Output Ripple
I_{OUT} = 0A
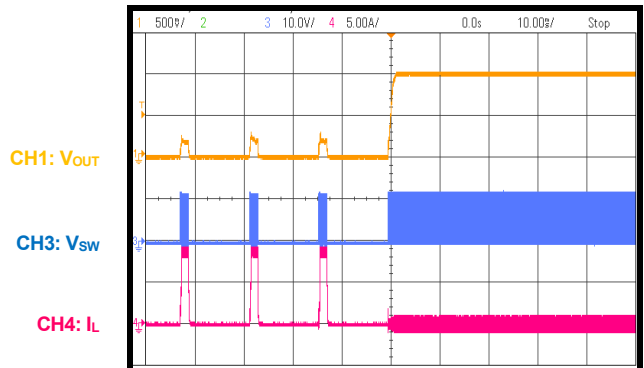
Input and Output Ripple
I_{OUT} = 6A

Short-Circuit Entry
I_{OUT} = 0A

Short-Circuit Recovery
I_{OUT} = 0A

TYPICAL PERFORMANCE CHARACTERISTICS *(continued)*

Performance waveforms are tested on the evaluation board from the Design Example section on page 15. V$_{IN}$ = 12V, V$_{OUT}$ = 1V, T$_A$ = 25°C, unless otherwise noted.

Short-Circuit Entry
I$_{OUT}$ = 6A

CH1: V$_{OUT}$
CH3: V$_{SW}$
CH4: I$_L$
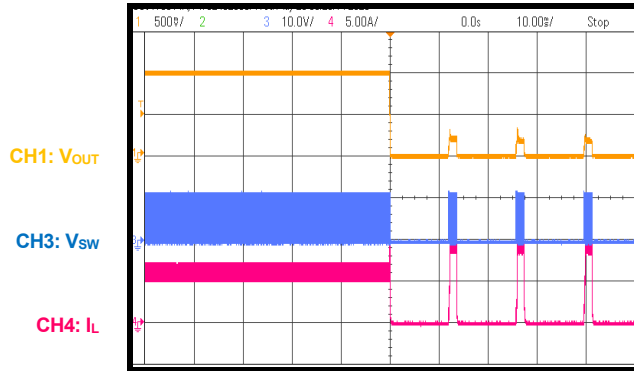
Short-Circuit Recovery
I$_{OUT}$ = 6A

CH1: V$_{OUT}$
CH3: V$_{SW}$
CH4: I$_L$
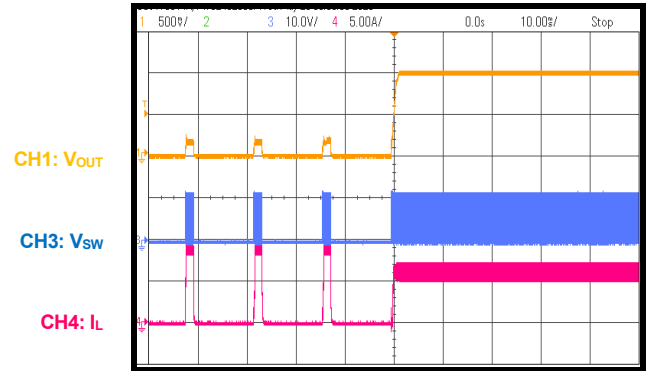
Transient Response
I$_{OUT}$ = 3A to 6A, slew rate = 2.5A/µs by e-load

CH1: V$_{OUT}$/AC
CH4: I$_{OUT}$
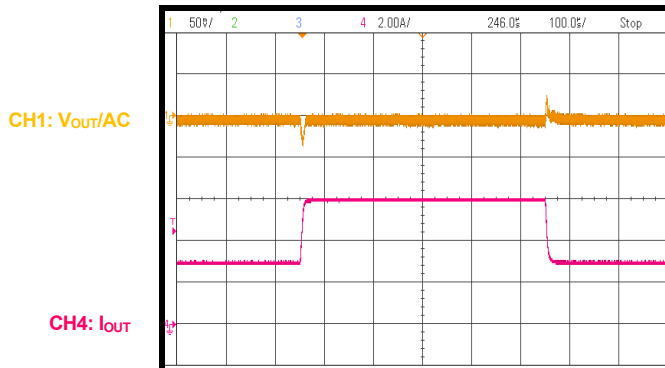
FUNCTIONAL BLOCK DIAGRAM

Figure 1: Functional Block Diagram

OPERATION

The MP2236C is a fully integrated, synchronous, rectified, step-down, switch-mode converter. The device uses constant-on-time (COT) control to provide fast transient response and ease loop stabilization. Figure 2 shows the simplified ramp compensation block in the MP2236C.
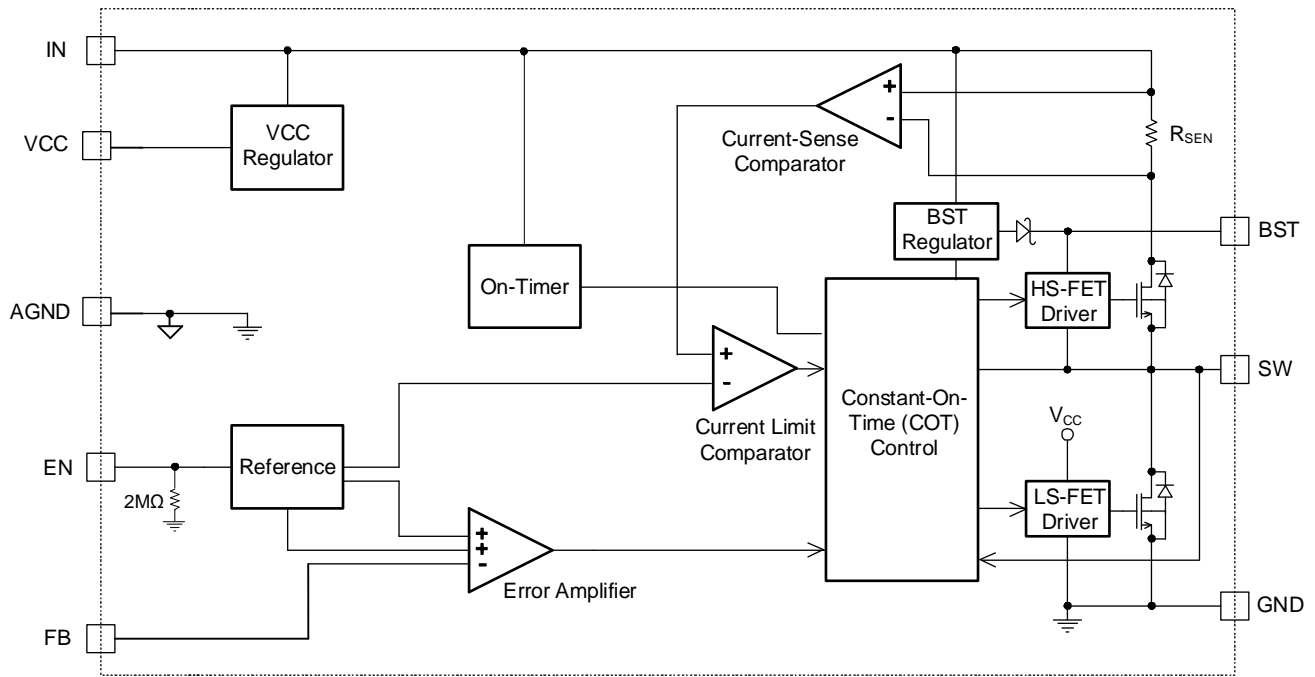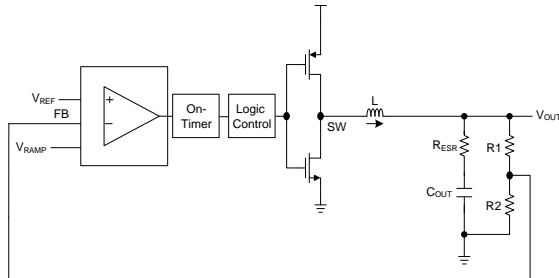

Figure 2: Simplified Compensation Block

At the beginning of each cycle, the high-side MOSFET (HS-FET) turns on whenever the ramp voltage (V_{RAMP}) is below the error amplifier (EA)'s output voltage (V_{EAO}), which indicates an insufficient output voltage (V_{OUT}). The on period is determined by both V_{OUT} and the input voltage (V_{IN}) to make the switching frequency (f_{SW}) fairly constant across the entire V_{IN} range.

After the on period elapses, the HS-FET turns off. By cycling the HS-FET on and off, the converter regulates V_{OUT}. The integrated low-side MOSFET (LS-FET) turns on when the HS-FET is off to minimize conduction loss.

If the HS-FET and LS-FET are turned on at the same time, a dead short occurs between the input and GND; this is called shoot-through. To avoid significantly reduced efficiency from shoot-through, the MP2236C generates a dead time (DT) internally between the HS-FET off period and LS-FET on period, and vice versa.

Error Amplifier (EA)

The EA compares the FB voltage (V_{FB}) against the internal 0.6V reference voltage (V_{REF}) and outputs a pulse-width modulation (PWM) signal. The optimized internal ramp compensation minimizes the external component count and simplifies control loop design.

Enable (EN)

EN is a digital control pin that turns the regulator on and off. Pull EN high to turn on the regulator. Pull EN low to turn off the regulator. An internal 2MΩ resistor is connected from EN to ground. EN can operate with a 20V V_{IN}, which allows EN to be connected directly to V_{IN} for automatic start-up.

Under-Voltage Lockout (UVLO)

Under-voltage lockout (UVLO) protects the chip from operating with an insufficient supply voltage. The MP2236C's UVLO comparator monitors V_{IN}. The MP2236C is active when V_{IN} exceeds the UVLO rising threshold.

Soft Start (SS) and Pre-Biased Start-Up

Soft start (SS) prevents the converter's V_{OUT} from overshooting during start-up. When the chip starts up, the internal circuitry generates a soft-start voltage (V_{SS}) that ramps up from 0V to the internal V_{CC}. When V_{SS} is below V_{REF}, the EA uses V_{SS} as the reference. When V_{SS} exceeds V_{REF}, V_{REF} takes over as the reference.

The soft-start time (t_{SS}) is set to 1ms internally. If the MP2236C's output is pre-biased to a certain voltage during start-up, the IC disables the HS-FET and LS-FET switching until the voltage on the internal SS capacitor (C_{SS}) exceeds the sensed V_{OUT} at FB.

Low-Dropout (LDO) Operation

To improve dropout, the MP2236C is designed to extend its on time if the duty cycle exceeds 85%. When the HS-FET on time is extended, the frequency drops. The typical minimum frequency (f_{SW_MIN}) is 260kHz. When the frequency drops to 260kHz, it cannot reduce any further and the HS-FET off time begins decreasing. The duty cycle reaches its maximum (D_{MAX}) when the off time is at its minimum value. If V_{IN} drops, the MP2236C operates at D_{MAX} and V_{OUT} drops.

The typical D_{MAX} can be calculated using Equation (1):

$$D_{MAX} = 1 - t_{OFF\_MIN} \times f_{SW\_MIN} \qquad (1)$$

Where the minimum off time (t_{OFF_MIN}) is 170ns, and f_{SW_MIN} is 260kHz.

Over-Current Protection (OCP) and Hiccup Mode

The MP2236C offers cycle-by-cycle, over-current (OC) limiting control. The current-limit circuit employs a low-side (LS) valley current-sensing algorithm. The MP2236C uses the LS-FET on resistance ($R_{DS(ON)}$) as a current-sensing element for valley-current limiting. When the LS-FET turns on, the inductor current (I_L) is monitored by the voltage between GND and SW. As the positive current-sensing node, GND must be connected to the bottom MOSFET's source terminal. PWM cannot initiate a new cycle until I_L falls to the valley threshold.

After the cycle-by-cycle OC limit is reached, V_{OUT} drops until it is below the under-voltage (UV) threshold. There are two UV thresholds: UV1 (80%) and UV2 (60%). Once UV1 and OC are both triggered, the MP2236C waits for 30 cycles. If OC exits after 31 cycles, then the MP2236C enters hiccup mode to periodically restart the part with a 12.5% duty cycle. If UV2 and OC are triggered, then the MP2236C enters hiccup mode after three cycles. This protection mode is especially useful when the output is dead-shorted to ground. The average short-circuit current is greatly reduced to alleviate thermal issues and protect the regulator. Once the OC condition is removed, the MP2236C exits hiccup mode and resumes normal operation.

Thermal Shutdown

Thermal shutdown prevents the chip from operating at exceedingly high temperatures. If the silicon die temperature exceeds 150°C, the entire chip shuts down. Once the temperature drops below its lower threshold (typically 130°C), the chip is enabled again.

Floating Driver and Bootstrap (BST) Charging

An external bootstrap (BST) capacitor (C_{BST}) powers the floating power MOSFET driver, which has its own UVLO protection. The UVLO rising threshold is 1.2V, with a 150mV hysteresis. The C_{BST} voltage is regulated internally by V_{IN} through D1, M1, C4, L1, and C2 (see Figure 3).
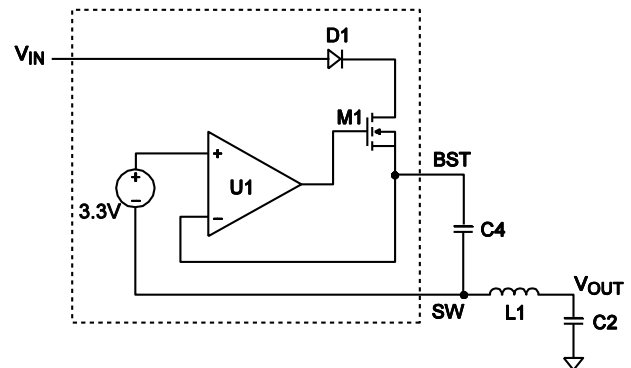
Figure 3: Internal BST Charging Circuit

If V_{IN} - V_{SW} exceeds 3.3V, then U1 regulates M1 to maintain a 3.3V BST voltage across C4.

Start-Up and Shutdown

If both V_{IN} and EN exceed their respective thresholds, the chip starts up. The reference block starts first, generating a stable V_{REF} and current, and then the internal regulator is enabled. The regulator provides a stable supply for the remaining circuitries.

Three events can shut down the chip: EN low, V_{IN} low, and thermal shutdown. During the shutdown procedure, the signaling path is blocked first to avoid any fault triggering. Then the internal supply rail is pulled down.

APPLICATION INFORMATION

Setting the Output Voltage (V_{OUT})

An external resistor divider can set V_{OUT} through FB. R1 and R2 can be calculated using Equation (2):

$$R2 = \frac{R1}{\frac{V_{OUT}}{0.6V} - 1} \qquad (2)$$

Table 1 lists the recommended feedback (FB) resistor values for common output voltages.

Table 1: Resistor Selection for Common Output Voltages

V_{OUT} (V)	R1 (kΩ)	R2 (kΩ)
1.0	28.7	43
1.8	86.6	43
2.5	100	31.6
3.3	100	22.1
5	100	13.7

Selecting the Inductor

MPL **Optimized Performance with MPS Inductor MPL-AL6050 Series**

For most applications, it is recommended use a 0.47µH to 10µH inductor with a DC current rating at least 25% above the maximum load current. For the highest efficiency, use an inductor with a DC resistance below 15mΩ. For most designs, the inductance (L_1) can be derived using Equation (3):

$$L_1 = \frac{V_{OUT} \times (V_{IN} - V_{OUT})}{V_{IN} \times \Delta I_L \times f_{SW}} \qquad (3)$$

Where ΔI_L is the inductor ripple current.

Set the inductor ripple current to be approximately 30% of the maximum load current. The maximum inductor peak current ($I_{L(MAX)}$) can be calculated using Equation (4):

$$I_{L(MAX)} = I_{LOAD} + \frac{\Delta I_L}{2} \qquad (4)$$

Use a larger-value inductor for improved efficiency under light-load conditions below 100mA.

MPS inductors are optimized and tested for use with a complete line of integrated circuits.

Table 2 lists our power inductor recommendations. Select a part number based on the design requirements.

Table 2: Power Inductor Selection

Part Number	Inductance	Manufacturer
MPL-AL6050-3R3	3.3µH	MPS
MPL-AL6050-2R2	2.2µH	MPS
MPL-AL6050-1R5	1.5µH	MPS
MPL-AL6050-1R0	1.0µH	MPS

Visit MonolithicPower.com under Products > Inductors for more information.

Selecting the Input Capacitor (C_{IN})

The step-down converter has a discontinuous input current (I_{IN}), and requires a capacitor to supply AC current while maintaining the DC V_{IN}. Use low-ESR capacitors for the best performance. Ceramic capacitors with X5R or X7R dielectrics are recommended because of their low ESR and small temperature coefficients. For most applications, use two 22µF capacitors.

Since C1 absorbs the input switching current, it requires an adequate ripple current rating. The RMS current in C_{IN} (I_{C1}) can be estimated using Equation (5):

$$I_{C1} = I_{LOAD} \times \sqrt{\frac{V_{OUT}}{V_{IN}} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right)} \qquad (5)$$

The worst-case condition occurs at $V_{IN} = 2 \times V_{OUT}$, which can be calculated with Equation (6):

$$I_{C1} = \frac{I_{LOAD}}{2} \qquad (6)$$

For simplification, choose a C_{IN} with an RMS current rating that exceeds half of the maximum load current.

C_{IN} can be electrolytic, tantalum, or ceramic. When using electrolytic or tantalum capacitors, add a small, high-quality ceramic capacitor (e.g. 0.1µF) as close to the IC as possible. When using ceramic capacitors, ensure that they have enough capacitance to provide a sufficient charge to prevent excessive voltage ripple at the input.

The input voltage ripple (ΔV_{IN}) caused by the capacitance can be estimated using Equation (7):

$$\Delta V_{IN} = \frac{I_{LOAD}}{f_{SW} \times C1} \times \frac{V_{OUT}}{V_{IN}} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right) \qquad (7)$$

Selecting the Output Capacitor (C_{OUT})

The traditional COT control scheme is intrinsically unstable if the output capacitor's (C_{OUT}) ESR is not high enough to act as an effective current-sense resistor. The MP2236C uses built-in, internal ramp compensation to ensure that the system is stable even without the help of C_{OUT}'s ESR. A pure ceramic capacitor solution can reduce the output ripple, total BOM cost, and board area significantly.

C_{OUT} maintains the DC V_{OUT}. Use ceramic, tantalum, or low-ESR electrolytic capacitors. For the best results, use low-ESR capacitors to keep the output voltage ripple low. The output voltage ripple (ΔV_{OUT}) can be estimated using Equation (8):

$$\Delta V_{OUT} = \frac{V_{OUT}}{f_{SW} \times L_1} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right) \times \left(R_{ESR} + \frac{1}{8 \times f_{SW} \times C2}\right)(8)$$

Where L_1 is the inductance, R_{ESR} is C_{OUT}'s ESR value, and C2 is C_{OUT}.

For ceramic capacitors, the capacitance dominates the impedance at f_{SW} and causes the majority of ΔV_{OUT}. For simplification, ΔV_{OUT} can be estimated using Equation (9):

$$\Delta V_{OUT} = \frac{V_{OUT}}{8 \times f_{SW}^2 \times L_1 \times C2} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right) \qquad (9)$$

For tantalum or electrolytic capacitors, the ESR dominates the impedance at f_{SW}. For simplification, ΔV_{OUT} can be approximated using Equation (10):

$$\Delta V_{OUT} = \frac{V_{OUT}}{f_{SW} \times L_1} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right) \times R_{ESR} \qquad (10)$$

The C_{OUT} characteristics also affect the stability of the regulation system. The MP2236C can be optimized for a wide range of capacitances and ESR values.

External Bootstrap (BST) Diode

An external BST diode can enhance the efficiency of the regulator, given the following conditions:

- V_{IN} is below 5V

- V_{OUT} is 3.3V

- Duty cycle is high: $D = \dfrac{V_{OUT}}{V_{IN}} > 65\%$

If these conditions are met, add an external BST diode from VCC to BST (see Figure 4).
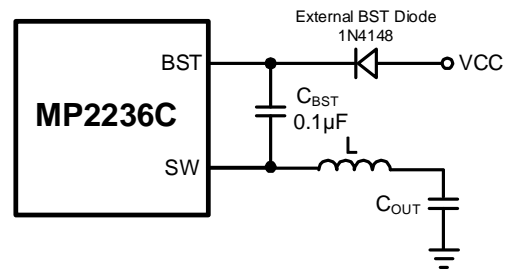
Figure 4: Optional External BST Diode to Enhance Efficiency

The recommended external BST diode is 1N4148, and the recommended C_{BST} value is 0.1µF.

Design Example

Table 3 shows a design example following the application guidelines for the specifications below.

Table 2: Design Example

V_{IN}	V_{OUT}	I_{OUT}
12V	1V	6A

For the detailed application schematics, see Figure 6, Figure 7, Figure 8, Figure 9, and Figure 10 on pages 17 and 18. For the typical performance and circuit waveforms, see the Typical Performance Characteristics section on page 8. For more device applications, refer to the related evaluation board datasheets.

PCB Layout Guidelines [9]

Efficient PCB layout is critical for stable operation. For the best results, refer to Figure 5 and follow the guidelines below:

1. Connect the input ground to GND using the shortest and widest trace possible.

2. Connect C_{IN} to IN using the shortest and widest trace possible.

3. Ensure that all FB connections are short and direct.

4. Place the FB resistors and compensation components as close to the chip as possible.

5. Route SW away from sensitive analog areas, such as VOUT.

6. Connect AGND to PGND using the shortest and widest trace possible.

Note:

9) The recommended layout is based on the Typical Application Circuits shown in Figure 6, Figure 7, Figure 8, Figure 9, and Figure 10 on pages 17 and 18.
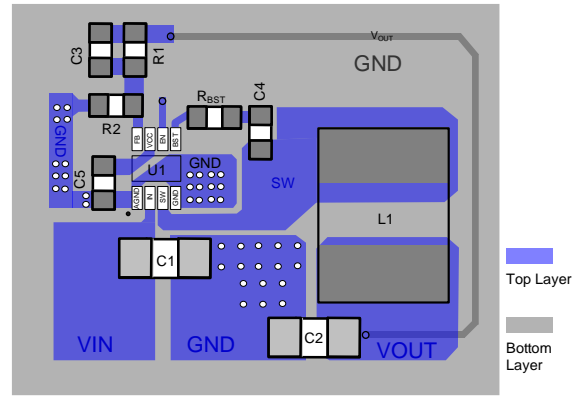
Figure 5: Recommended PCB Layout

TYPICAL APPLICATION CIRCUITS
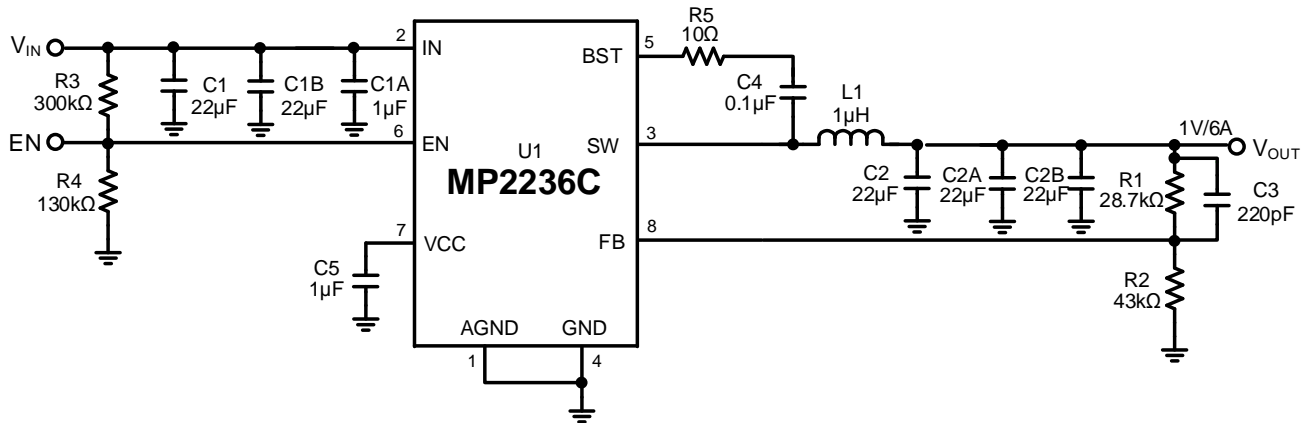
Figure 6: Typical Application Circuit (12V V$_{IN}$, 1V/6A Output)
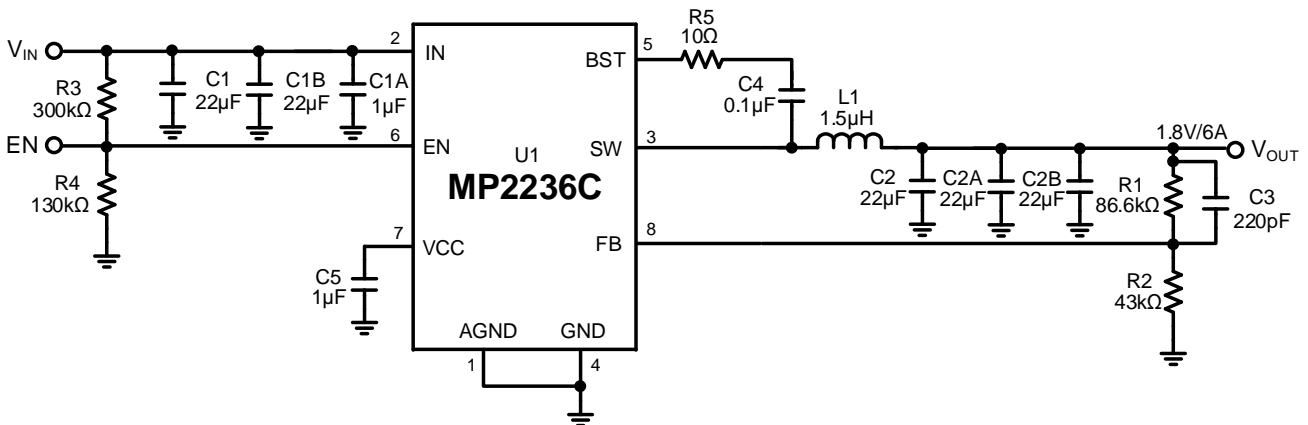
Figure 7: Typical Application Circuit (12V V$_{IN}$, 1.8V/6A Output)
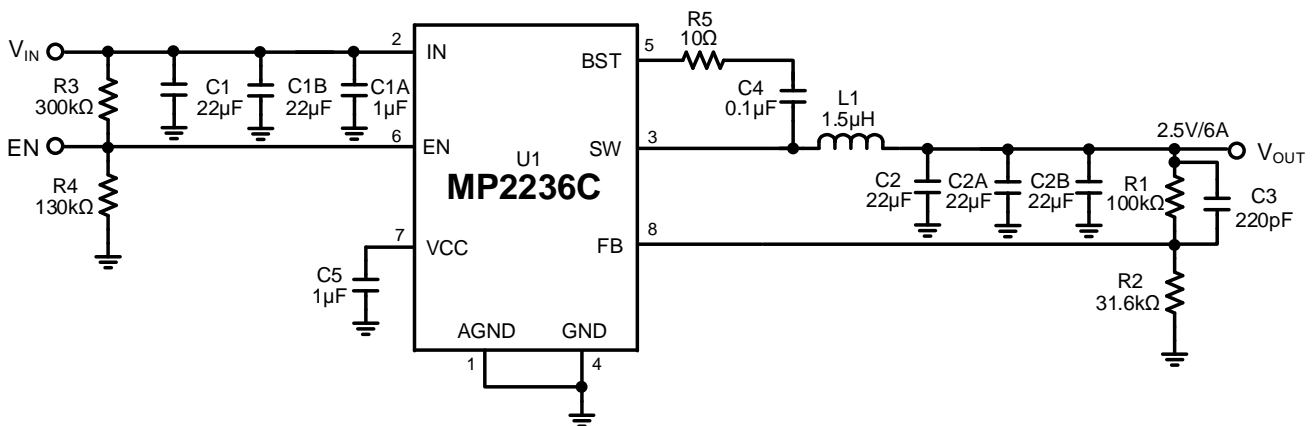
Figure 8: Typical Application Circuit (12V V$_{IN}$, 2.5V/6A Output)
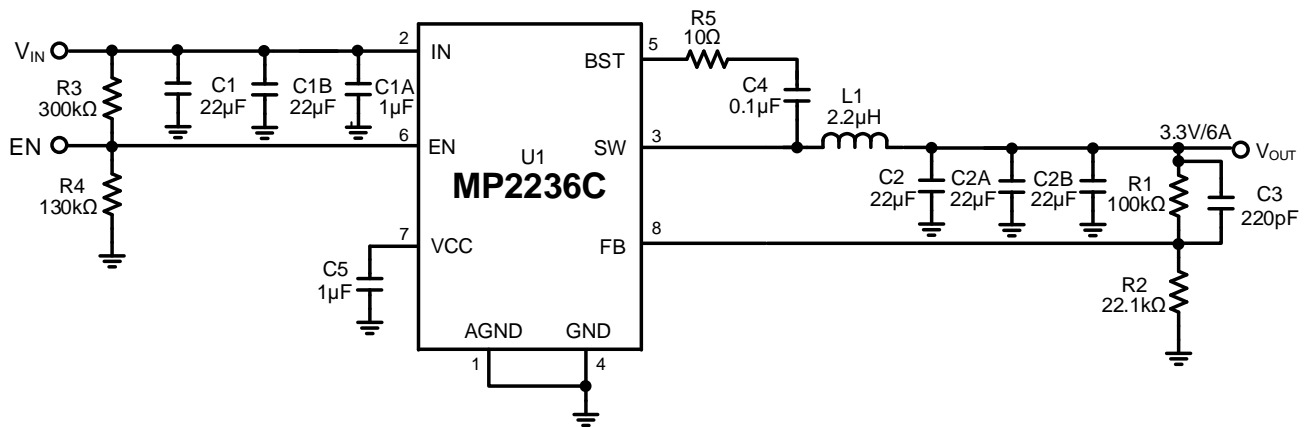
TYPICAL APPLICATION CIRCUITS *(continued)*

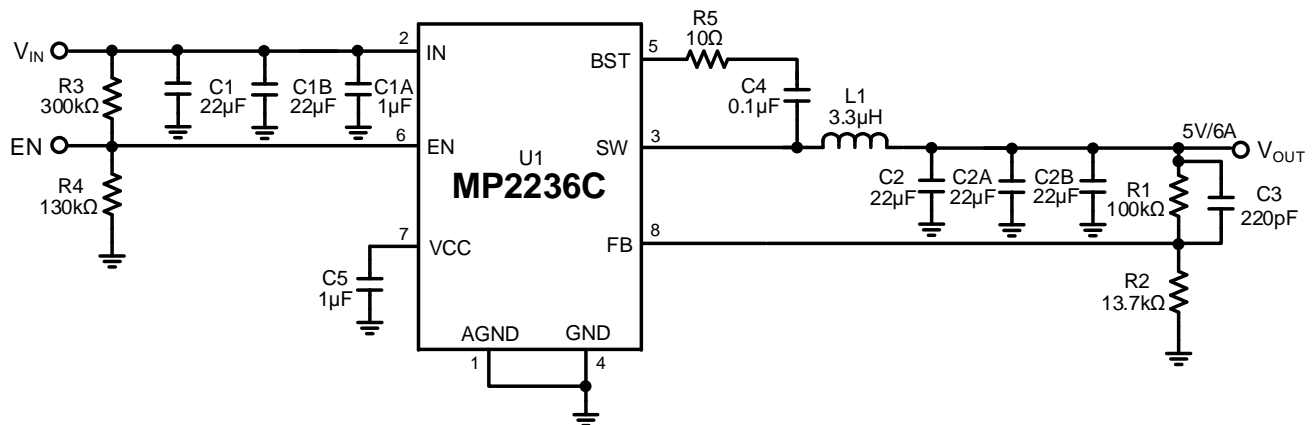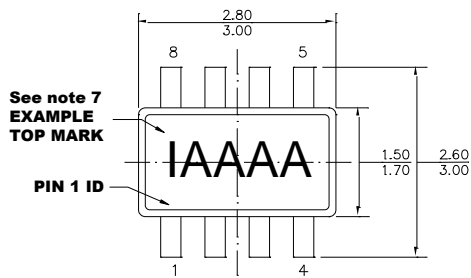**Figure 9: Typical Application Circuit (12V V_{IN}, 3.3V/6A Output)**

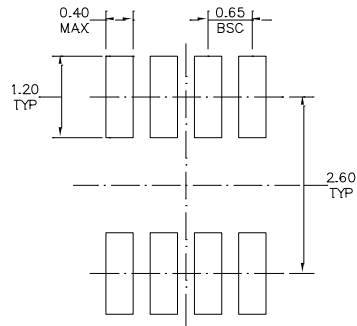**Figure 10: Typical Application Circuit (12V V_{IN}, 5V/6A Output)**

PACKAGE INFORMATION
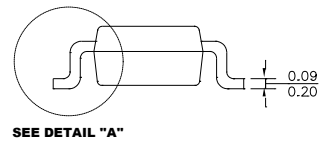
TSOT23-8
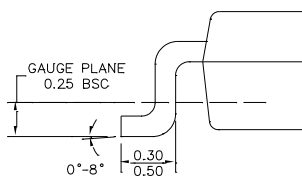

TOP VIEW

RECOMMENDED LAND PATTERN

FRONT VIEW

SEE DETAIL "A"
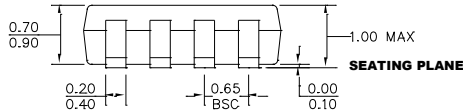
SIDE VIEW

**DETAIL "A"**

NOTE:

1) ALL DIMENSIONS ARE IN MILLIMETERS.
2) PACKAGE LENGTH DOES NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURR.
3) PACKAGE WIDTH DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
4) LEAD COPLANARITY (BOTTOM OF LEADS AFTER FORMING) SHALL BE 0.10 MILLIMETERS MAX.
5) JEDEC REFERENCE IS MO-193, VARIATION BA.
6) DRAWING IS NOT TO SCALE.
7) PIN 1 IS LOWER LEFT PIN WHEN READING TOP MARK FROM LEFT TO RIGHT, (SEE EXAMPLE TOP MARK)

CARRIER INFORMATION
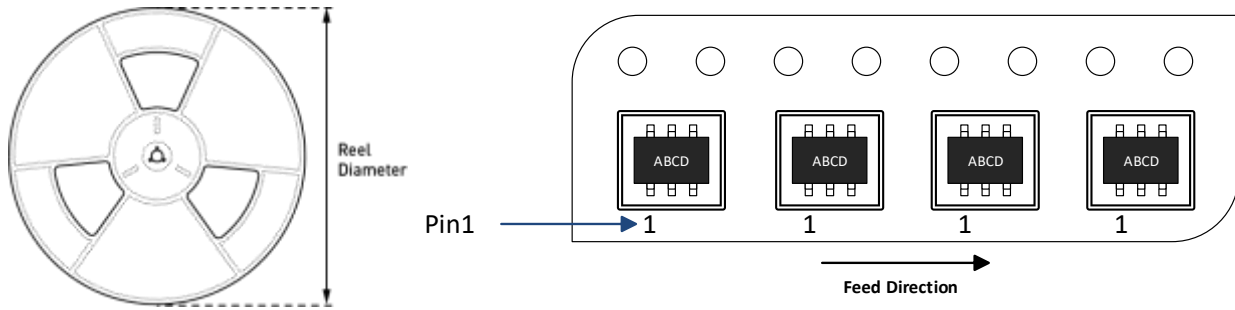
Part Number	Package Description	Quantity/ Reel	Quantity/ Tube	Quantity/ Tray	Reel Diameter	Carrier Tape Width	Carrier Tape Pitch
MP2236CGJ-Z	TSOT23-8	3000	N/A	N/A	7in	8mm	4mm

REVISION HISTORY

Revision #	Revision Date	Description	Pages Updated
1.0	3/16/2022	Initial Release	-

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[Monolithic Power Systems (MPS)](#):
  [MP2236CGJ-P](#) [MP2236CGJ-Z](#)